

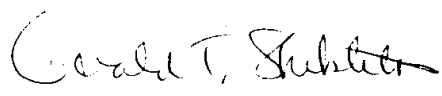
A¹
4. (amended) A silicon single crystal wafer with decreased gown-in defects, which is obtained from said silicon single crystal ingot according to Claim 1.

5. (amended) A silicon perfect single crystal wafer free from grown-in defects, which is obtained from said silicon single crystal ingot according to Claim 1.

A²
23. (amended) The CZ method-based single crystal ingot production device according to Claim 17, characterized in that said single crystal ingot is a single crystal ingot, including a portion of a perfect crystal.

Respectfully submitted,

WELSH & KATZ, LTD.


By
Gerald T. Shekleton
Registration No. 27,466

Dated: May 18, 2001

Welsh & Katz, Ltd.
120 South Riverside Plaza
22nd Floor
Chicago, Illinois 60606
Telephone: 312/655-1500